

RUGGED METAL ELECTRODES FOR METAL-INSULATOR-METAL CAPACITORS

Abstract of the Disclosure

Thin film metal-insulator-metal capacitors having enhanced surface area are formed by a substituting metal for silicon in a preformed electrode geometry. The resulting metal structures are advantageous for high-density DRAM applications since they have good conductivity, enhanced surface area and are compatible with capacitor dielectric materials having high dielectric constant.

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